



NEC's NPN MEDIUM POWER MICROWAVE TRANSISTOR

NE46100 NE46134

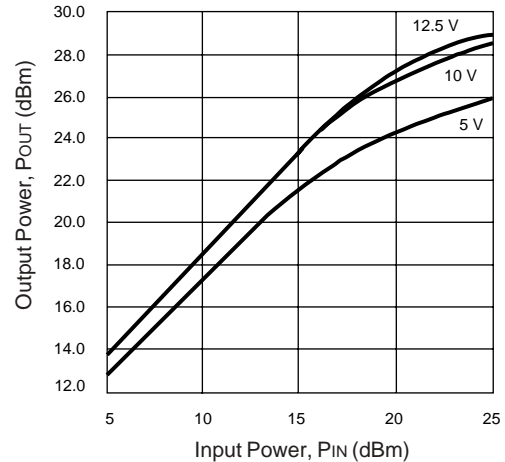
FEATURES

- HIGH DYNAMIC RANGE
- LOW IM DISTORTION: -40 dBc
- HIGH OUTPUT POWER : 27.5 dBm at TYP
- LOW NOISE: 1.5 dB TYP at 500 MHz
- LOW COST

DESCRIPTION

NEC's NE461 series of NPN silicon epitaxial bipolar transistors is designed for medium power applications requiring high dynamic range. This device exhibits an outstanding combination of high gain and low intermodulation distortion, as well as low noise figure. The NE461 series offers excellent performance and reliability at low cost through NEC's titanium, platinum, gold metallization system and direct nitride passivation of the surface of the chip. Devices are available in a low cost surface mount package (SOT-89) as well as in chip form.

NE46134
TYPICAL OUTPUT POWER
vs. INPUT POWER
f = 1.0 GHz, I_c = 100 mA



ELECTRICAL CHARACTERISTICS (T_A = 25°C)

PART NUMBER EIAJ ¹ REGISTERED NUMBER PACKAGE OUTLINE			NE46100 00 (CHIP)			NE46134 2SC4536 34		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX	MIN	TYP	MAX
f _T	Gain Bandwidth Product at V _{CE} = 10 V, I _c = 100 mA	GHz		5.5			5.5	
NF _{MIN}	Minimum Noise Figure ³ at V _{CE} = 10 V, I _c = 50 mA, 500 MHz V _{CE} = 10 V, I _c = 50 mA, 1 GHz	dB dB		1.5 2.0			1.5 2.0	
GL	Linear Gain, V _{CE} = 12.5 V, I _c = 100 mA, 2.0 GHz V _{CE} = 12.5 V, I _c = 100 mA, 1.0 GHz	dB dB		9.0			8.0	
S _{21E} ²	Insertion Power Gain at 10 V, 50 mA, f = 1.0 GHz	dB		10.0		5.5	7.0	
h _{FE}	DC Current Gain ² at V _{CE} = 10 V, I _c = 50 mA		40		200	40		200
I _{CBO}	Collector Cutoff Current at V _{CB} = 20 V, I _E = 0 mA	μA			5.0			5.0
I _{EBO}	Emitter Cutoff Current at V _{EB} = 2 V, I _C = 0 mA	μA			5.0			5.0
P _{1dB}	Output Power at 1 dB Compression, V _{CE} = 12.5 V, I _c = 100 mA, 2.0 GHz V _{CE} = 12.5 V, I _c = 100 mA, 1.0 GHz	dBm dBm	27.0				27.5	
IM ₃	Intermodulation Distortion, 10 V, 100 mA, F ₁ = 1.0 GHz, F ₂ = 0.99 GHz, Total P _{OUT} = 20 dBm	dBc	-40.0			-40.0		
R _{TH} (J-C)	Thermal Resistance (Junction to Case)	°C/W			30			32.5
R _{TH} (J-A)	Thermal Resistance (Junction to Ambient)	°C/W					312.5	

Notes:

1. Electronic Industrial Association of Japan.
2. Pulsed: PW ≤ 350 ms, Duty Cycle ≤ 2%
3. RS = RL = 50 Ω untuned

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CB0}	Collector to Base Voltage	V	30
V _{CE0}	Collector to Emitter Voltage	V	15
V _{EBO}	Emitter to Base Voltage	V	3
I _C	Collector Current	mA	250
P _T	Total Power Dissipation	W	3.75
	NE46100 ²	W	2.0
T _J	Junction Temperature	°C	200
	NE46134	°C	150
T _{STG}	Storage Temperature	°C	-65 to +200
	NE46134	°C	-65 to +150

Notes:

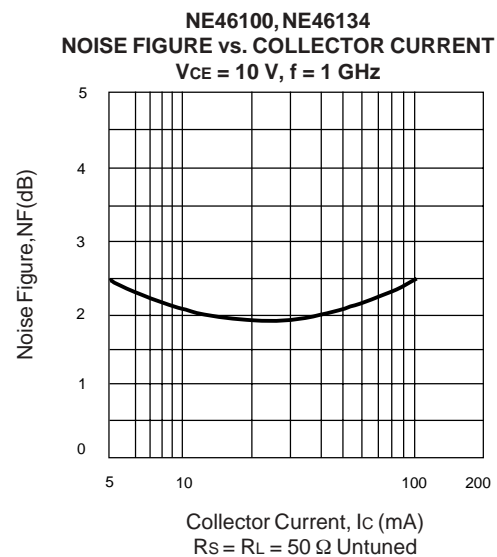
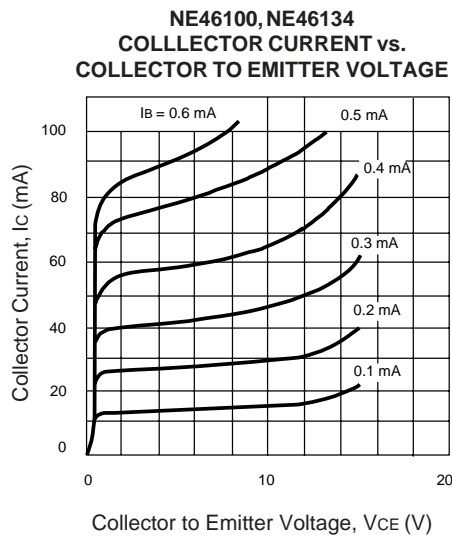
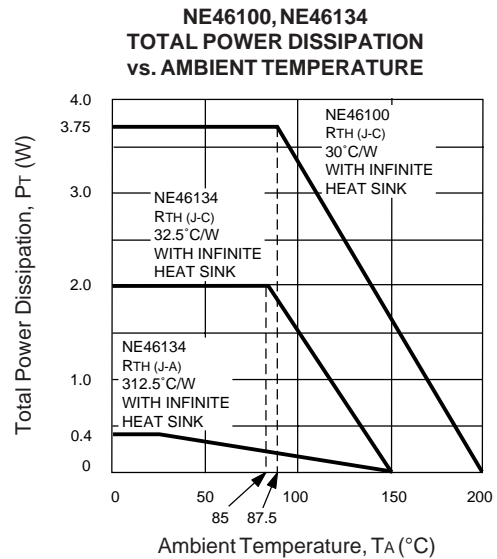
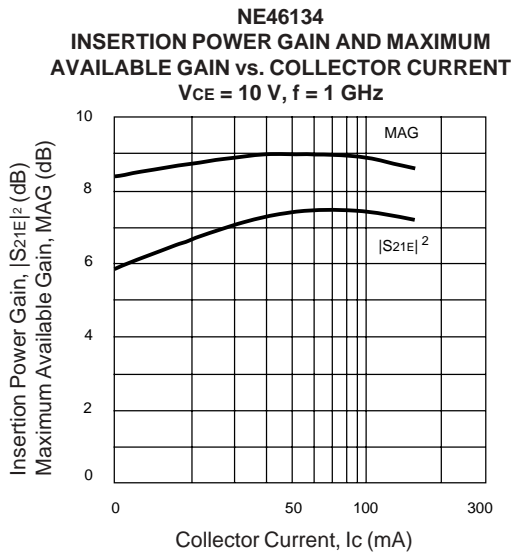
1. Operation in excess of any one of these parameters may result in permanent damage.
2. Chip mounted on an infinite heat sink (see AN-1001 for handling instructions).
3. Packaged device mounted on 0.7 mm x 2.5 cm² double sided ceramic substrate (copper plating).

NE46134

TYPICAL NOISE PARAMETERS (T_A = 25°C)

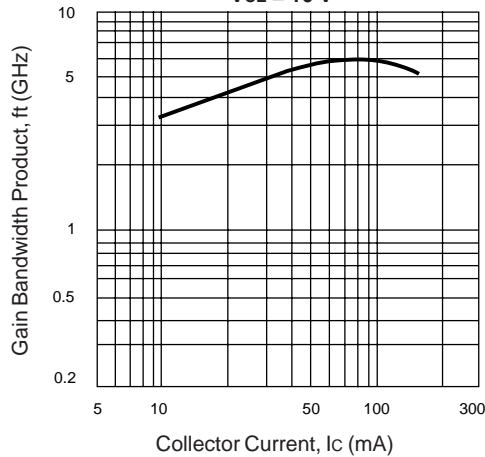
FREQ. (GHz)	NF _{OPT} (dB)	G _A (dB)	Γ _{OPT}		RN/50
			MAG	ANG	
V _{CC} = 10 V, I _C = 50 mA					
0.5	1.5	13.5	0.34	-176	0.09

TYPICAL PERFORMANCE CURVES (T_A=25°C)

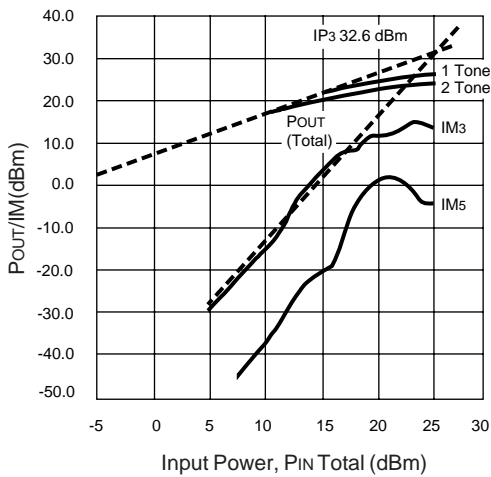


TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)

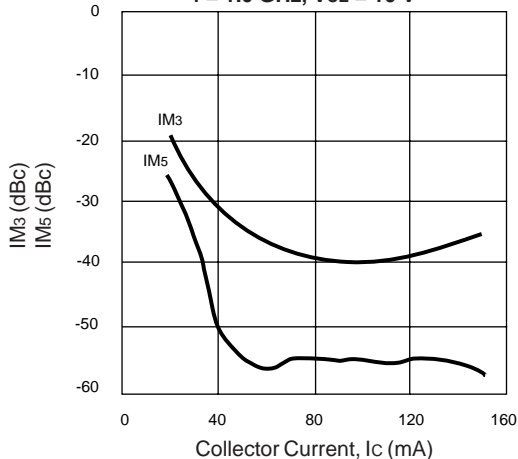
NE46100, NE46134
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT
 $V_{CE} = 10\text{ V}$



NE46134
TYPICAL OUTPUT POWER/INTERMODULATION DISTORTION vs. INPUT POWER
 $f = 1.0\text{ GHz}$, $V_{CE} = 10\text{ V}$, $I_C = 100\text{ mA}$
2 Tone Test $F_1 = 1.0\text{ GHz}$, $F_2 = 0.99\text{ GHz}$

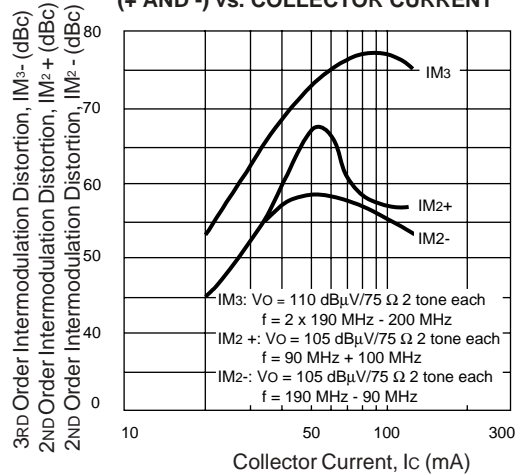


NE46100, NE46134
INTERMODULATION DISTORTION vs. COLLECTOR CURRENT
 $f = 1.0\text{ GHz}$, $V_{CE} = 10\text{ V}$

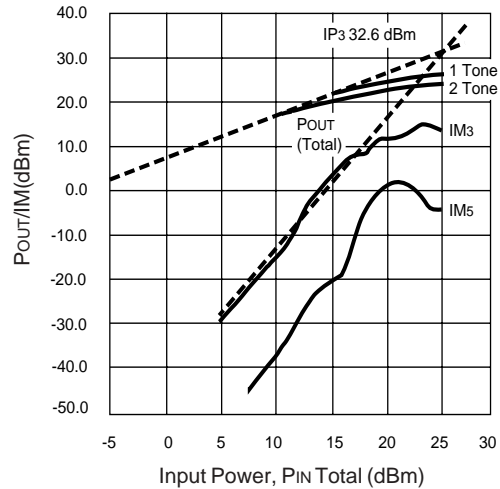


2 Tone Test
 Total $P_{IN} = 12.1\text{ dBm}$
 $F_1 = 1.0\text{ GHz}$, $F_2 = 0.99\text{ GHz}$

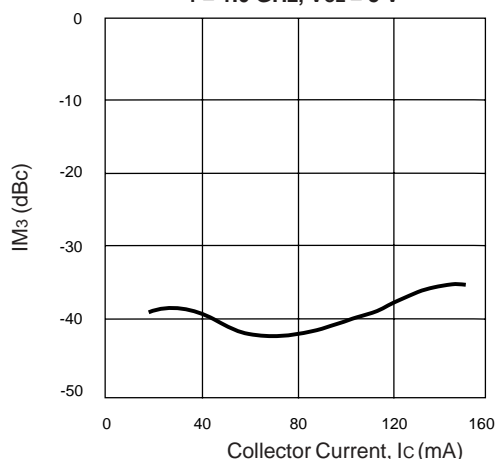
NE46134
3RD ORDER INTERMODULATION DISTORTION, 2ND ORDER INTERMODULATION DISTORTION (+ AND -) vs. COLLECTOR CURRENT



NE46134
TYPICAL OUTPUT POWER/INTERMODULATION DISTORTION vs. INPUT POWER
 $f = 1.0\text{ GHz}$, $V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$
2 Tone Test $F_1 = 1.0\text{ GHz}$, $F_2 = 0.99\text{ GHz}$

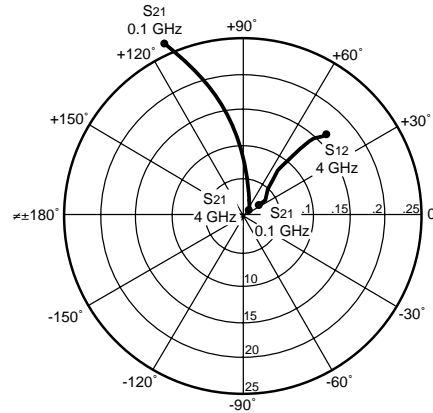
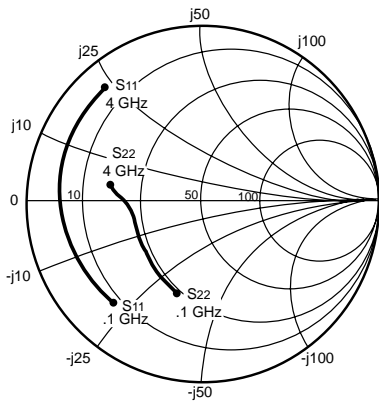


NE46100, NE46134
INTERMODULATION DISTORTION vs. COLLECTOR CURRENT
 $f = 1.0\text{ GHz}$, $V_{CE} = 5\text{ V}$



Total $P_{IN} = 6.0\text{ dBm}$
 $F_1 = 1.0\text{ GHz}$, $F_2 = 0.99\text{ GHz}$
 Note: $IM_5 >$ than 58 dB down from carrier for measured currents greater than 40 mA.

TYPICAL COMMON EMITTER SCATTERING PARAMETERS¹ (T_A = 25°C)



Coordinates in Ohms
Frequency in GHz
V_{CE} = 5 V, I_C = 50 mA

NE46100
V_{CE} = 5 V, I_C = 50 mA

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	MAG ² (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		
100	0.778	-137	26.776	114	0.028	30	0.555	-102	0.16	29.8
200	0.815	-159	14.407	100	0.035	29	0.434	-135	0.36	26.2
500	0.826	-177	5.855	84	0.040	38	0.400	-162	0.75	21.7
800	0.827	176	3.682	76	0.052	43	0.402	-169	0.91	18.5
1000	0.826	173	2.963	71	0.058	47	0.405	-172	1.02	16.3
1200	0.825	170	2.441	66	0.064	47	0.412	-174	1.08	14.0
1400	0.820	167	2.111	61	0.069	47	0.413	-176	1.17	12.4
1600	0.828	165	1.863	57	0.078	54	0.426	-177	1.15	11.4
1800	0.827	162	1.671	53	0.087	50	0.432	-178	1.14	10.6
2000	0.828	159	1.484	49	0.093	50	0.431	-180	1.17	9.5
2500	0.822	153	1.218	39	0.11	48	0.462	177	1.18	7.8
3000	0.818	148	1.010	30	0.135	46	0.490	174	1.16	6.3
3500	0.824	142	0.876	21	0.147	44	0.507	170	1.16	5.3
4000	0.812	137	0.762	13	0.168	38	0.535	167	1.14	4.3

V_{CE} = 5 V, I_C = 100 mA

100	0.778	-144	27.669	111	0.027	35	0.523	-114	0.27	30.2
200	0.820	-164	14.559	97	0.029	29	0.445	-144	0.42	27.0
500	0.832	-179	5.885	84	0.035	38	0.435	-166	0.81	22.2
800	0.833	175	3.691	76	0.048	45	0.435	-173	0.95	18.8
1000	0.831	172	2.980	71	0.056	51	0.437	-176	1.05	16.0
1200	0.836	169	2.464	67	0.061	52	0.432	-178	1.11	14.0
1400	0.829	166	2.121	61	0.072	53	0.447	-180	1.12	12.6
1600	0.831	164	1.867	58	0.080	54	0.445	179	1.14	11.4
1800	0.827	161	1.671	54	0.090	53	0.460	178	1.14	10.4
2000	0.830	159	1.499	49	0.096	52	0.456	176	1.15	9.6
2500	0.831	153	1.228	40	0.115	51	0.479	173	1.15	8.0
3000	0.821	147	1.018	31	0.134	48	0.504	170	1.18	6.3
3500	0.820	142	0.881	23	0.155	42	0.516	167	1.14	5.3
4000	0.812	136	0.779	14	0.170	41	0.543	164	1.16	4.2

Notes:

1. S-Parameters include Bond wires.

Base: Total 1 wire, 1 per Bond Pad, 0.0259" (658 μm) long each wire.
 Collector: Total 1 wire, 1 per Bond Pad, 0.0182" (463 μm) long each wire.
 Emitter: Total 2 wires, 1 per side, 0.0224" (569 μm) long each wire.
 Wire: 0.0007" (17.8 μm) dia., gold.

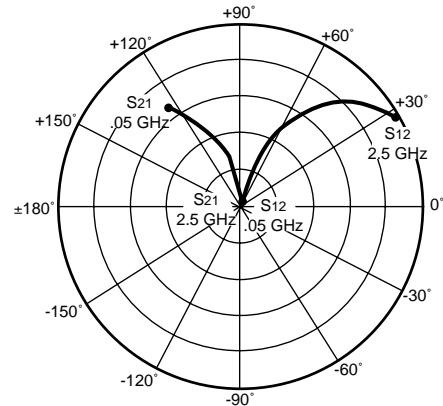
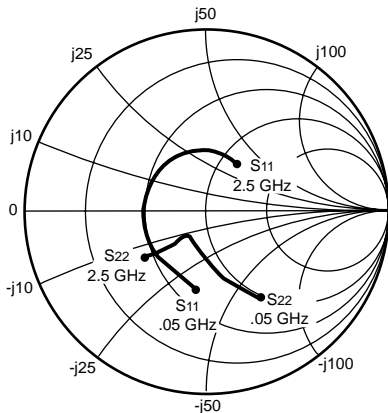
2. Gain Calculations:

$$\text{MAG} = \frac{|S_{21}|}{|S_{12}|} \left(K \pm \sqrt{K^2 - 1} \right). \text{ When } K \leq 1, \text{ MAG is undefined and MSG values are used. } \text{MSG} = \frac{|S_{21}|}{|S_{12}|}, K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}, \Delta = S_{11} S_{22} - S_{21} S_{12}$$

MAG = Maximum Available Gain

MSG = Maximum Stable Gain

TYPICAL COMMON EMITTER SCATTERING PARAMETERS (T_A = 25°C)



Coordinates in Ohms
Frequency in GHz
V_{CE} = 12.5 V, I_C = 50 mA

NE46134

V_{CE} = 12.5 V, I_C = 50 mA

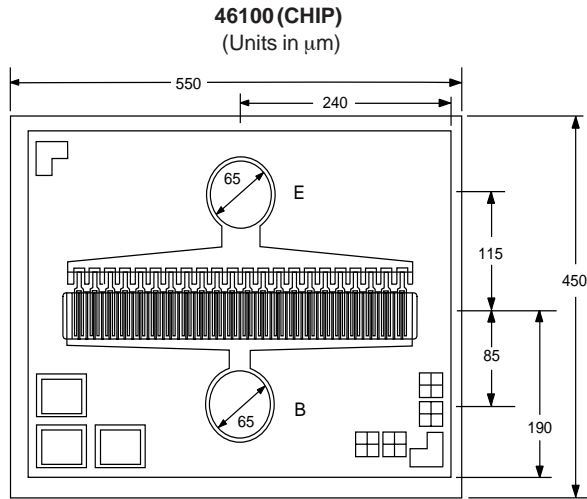
FREQUENCY (GHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	MAG ² (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		
0.05	0.432	-91.9	34.139	125.6	0.024	63.0	0.586	-56.7	0.50	31.5
0.10	0.372	-129.4	19.834	106.3	0.036	63.5	0.362	-78.4	0.75	27.4
0.20	0.348	-161.2	10.443	92.4	0.058	65.4	0.223	-97.1	0.95	22.6
0.40	0.343	173.5	5.332	79.3	0.104	68.1	0.170	-112.8	1.05	15.8
0.60	0.343	157.1	3.610	70.1	0.150	66.3	0.172	-119.3	1.07	12.2
0.80	0.349	143.8	2.755	61.8	0.196	63.1	0.188	-122.4	1.07	9.9
1.00	0.352	132.4	2.254	54.4	0.239	59.2	0.210	-124.2	1.07	8.2
1.20	0.353	121.2	1.927	47.1	0.280	55.0	0.236	-125.8	1.06	6.9
1.40	0.350	111.6	1.710	40.4	0.320	50.7	0.267	-127.4	1.05	6.0
1.60	0.343	101.9	1.523	34.0	0.354	46.2	0.300	-128.9	1.04	5.0
1.80	0.339	93.1	1.388	29.0	0.385	42.4	0.330	-131.5	1.04	4.3
2.00	0.336	83.3	1.295	23.5	0.418	38.2	0.357	-132.7	1.03	3.9
2.20	0.325	73.3	1.206	18.1	0.445	34.0	0.386	-134.0	1.03	3.3
2.40	0.318	63.0	1.140	13.6	0.471	29.9	0.411	-135.3	1.02	3.0
2.50	0.314	57.3	1.109	11.7	0.482	28.0	0.423	-135.9	1.02	2.7

V_{CE} = 12.5 V, I_C = 100 mA

0.05	0.380	-100.0	36.475	122.4	0.021	64.3	0.530	-62.6	0.59	32.4
0.10	0.355	-137.9	20.531	104.1	0.033	65.0	0.324	-86.1	0.82	27.9
0.20	0.341	-167.1	10.702	91.3	0.058	68.3	0.208	-106.6	0.97	22.7
0.40	0.338	170.0	5.446	79.0	0.106	69.6	0.167	-123.6	1.05	15.8
0.60	0.339	154.4	3.684	70.2	0.154	67.2	0.170	-129.1	1.06	12.3
0.80	0.344	141.3	2.812	62.1	0.201	63.5	0.185	-131.1	1.06	9.9
1.00	0.346	130.1	2.302	54.9	0.246	59.3	0.204	-131.7	1.06	8.2
1.20	0.349	119.2	1.971	47.8	0.288	54.9	0.229	-132.1	1.05	7.0
1.40	0.345	109.4	1.748	41.2	0.327	50.3	0.257	-132.7	1.04	6.0
1.60	0.336	99.7	1.557	34.9	0.362	45.7	0.288	-133.1	1.04	5.1
1.80	0.330	91.1	1.420	29.7	0.393	41.7	0.317	-135.0	1.04	4.3
2.00	0.328	80.3	1.324	24.6	0.426	37.4	0.343	-135.8	1.03	3.8
2.20	0.320	70.4	1.240	19.0	0.453	33.1	0.370	-136.5	1.03	3.4
2.40	0.309	60.2	1.170	14.4	0.478	29.0	0.395	-137.3	1.02	2.9
2.50	0.305	54.5	1.140	12.2	0.489	27.0	0.406	-137.8	1.02	2.7

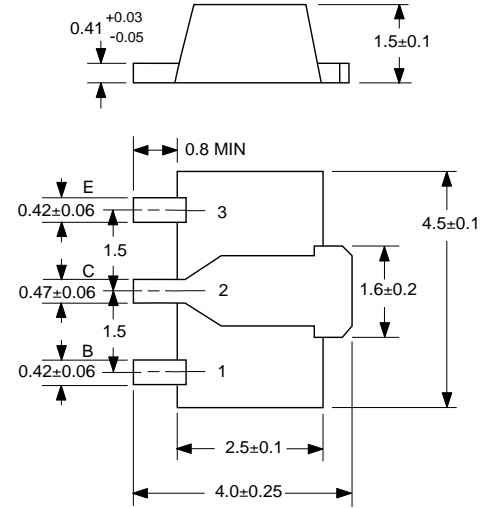
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OUTLINE DIMENSIONS



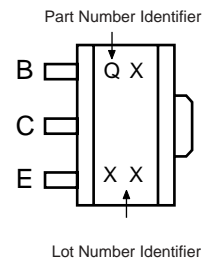
Thickness: 160 μm

PACKAGE OUTLINE 34 (SOT-89) (Units in mm)



BOTTOM VIEW

TOP VIEW



ORDERING INFORMATION

PART NUMBER	QUANTITY	PACKAGING
NE46100	100	Waffle Pack
NE46134-T1	1000	Tape & Reel

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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